

Ching-Hwa Ho

List of Publications by Year in descending order

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all docs

191
docs citations

191
times ranked

6810
citing authors

#	ARTICLE	IF	CITATIONS
1	Monolayer behaviour in bulk ReS ₂ due to electronic and vibrational decoupling. Nature Communications, 2014, 5, 3252.	12.8	906
2	Integrated digital inverters based on two-dimensional anisotropic ReS ₂ field-effect transistors. Nature Communications, 2015, 6, 6991.	12.8	505
3	Single-Layer ReS ₂ : Two-Dimensional Semiconductor with Tunable In-Plane Anisotropy. ACS Nano, 2015, 9, 11249-11257.	14.6	353
4	High-Mobility InSe Transistors: The Role of Surface Oxides. ACS Nano, 2017, 11, 7362-7370.	14.6	177
5	Formation and stability of point defects in monolayer rhenium disulfide. Physical Review B, 2014, 89, .	3.2	151
6	Disorder engineering and conductivity dome in ReS ₂ with electrolyte gating. Nature Communications, 2016, 7, 12391.	12.8	109
7	High Mobilities in Layered InSe Transistors with Indium-Encapsulation-Induced Surface Charge Doping. Advanced Materials, 2018, 30, e1803690.	21.0	101
8	The study of optical band edge property of bismuth oxide nanowires Bi_2O_3 . Optics Express, 2013, 21, 11965.	3.4	96
9	Absorption-edge anisotropy in ReS ₂ and ReSe ₂ layered semiconductors. Physical Review B, 1998, 58, 16130-16135.	3.2	94
10	Surface Oxide Effect on Optical Sensing and Photoelectric Conversion of In_2Se_3 Hexagonal Microplates. ACS Applied Materials & Interfaces, 2013, 5, 2269-2277.	8.0	91
11	Photoluminescence mechanisms of metallic Zn nanospheres, semiconducting ZnO nanoballoons and metal-semiconductor Zn/ZnO nanospheres. Scientific Reports, 2014, 4, 6967.	3.3	84
12	Oxidation-boosted charge trapping in ultra-sensitive van der Waals materials for artificial synaptic features. Nature Communications, 2020, 11, 2972.	12.8	83
13	Optical properties of the interband transitions of layered gallium sulfide. Journal of Applied Physics, 2006, 100, 083508.	2.5	78
14	Bending Photoluminescence and Surface Photovoltaic Effect on Multilayer InSe 2D Microplate Crystals. Advanced Optical Materials, 2015, 3, 1750-1758.	7.3	75
15	In-plane anisotropy of the optical and electrical properties of ReS ₂ and ReSe ₂ layered crystals. Journal of Alloys and Compounds, 2001, 317-318, 222-226.	5.5	70
16	Anisotropic Spectroscopy and Electrical Properties of 2D ReS ₂ ($1-x$)Se ₂ (x) Alloys with Distorted 1T Structure. Small, 2017, 13, 1603788.	10.0	70
17	Crystal structure and band-edge transitions of ReS ₂ $_{1-x}$ Se _x layered compounds. Journal of Physics and Chemistry of Solids, 1999, 60, 1797-1804.	4.0	69
18	Enhanced Photocatalytic Activity in Ga_2O_3 Nanobelts. Journal of the American Ceramic Society, 2011, 94, 3117-3122.	3.8	63

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19	Temperature dependence of energies and broadening parameters of the band-edge excitons of ReS ₂ and ReSe ₂ . <i>Physical Review B</i> , 1997, 55, 15608-15613.	3.2	60
20	High room-temperature photoluminescence of one-dimensional Ta ₂ O ₅ nanorod arrays. <i>Nanotechnology</i> , 2009, 20, 445708.	2.6	59
21	Direct Optical Observation of Band-Edge Excitons, Band Gap, and Fermi Level in Degenerate Semiconducting Oxide Nanowires In ₂ O ₃ . <i>Journal of Physical Chemistry C</i> , 2011, 115, 25088-25096.	3.1	58
22	In-plane anisotropy of the optical and electrical properties of layered ReS ₂ crystals. <i>Journal of Physics Condensed Matter</i> , 1999, 11, 5367-5375.	1.8	57
23	Thermoreflectance characterization of In ₂ -Ga ₂ O ₃ thin-film nanostrips. <i>Optics Express</i> , 2010, 18, 16360.	3.4	57
24	Enhanced photoelectric-conversion yield in niobium-incorporated In ₂ S ₃ with intermediate band. <i>Journal of Materials Chemistry</i> , 2011, 21, 10518.	6.7	57
25	Influence of anionic substitution on the electrolyte electroreflectance study of band edge transitions in single crystal Cu ₂ ZnSn(S _x Se _{1-x}) ₄ solid solutions. <i>Optical Materials</i> , 2012, 34, 1362-1365.	3.6	57
26	Optical absorption of ReS ₂ and ReSe ₂ single crystals. <i>Journal of Applied Physics</i> , 1997, 81, 6380-6383.	2.5	56
27	Electronic structure of ReS ₂ and ReSe ₂ from first-principles calculations, photoelectron spectroscopy, and electrolyte electroreflectance. <i>Physical Review B</i> , 1999, 60, 15766-15771.	3.2	56
28	Thickness-dependent carrier transport and optically enhanced transconductance gain in III-VI multilayer InSe. <i>2D Materials</i> , 2016, 3, 025019.	4.4	56
29	Growth and characterization of rhenium-doped MoS ₂ single crystals. <i>Journal of Crystal Growth</i> , 1999, 205, 543-547.	1.5	53
30	Pressure-induced metallization and superconducting phase in ReS ₂ . <i>Npj Quantum Materials</i> , 2017, 2, .	5.2	53
31	Growth and characterization of near-band-edge transitions in In ₂ -In ₂ S ₃ single crystals. <i>Journal of Crystal Growth</i> , 2010, 312, 2718-2723.	1.5	52
32	Optically decomposed near-band-edge structure and excitonic transitions in Ga ₂ S ₃ . <i>Scientific Reports</i> , 2014, 4, 6143.	3.3	52
33	Temperature dependence of energies and broadening parameters of the band-edge excitons of single crystals. <i>Journal of Physics Condensed Matter</i> , 1998, 10, 9317-9328.	1.8	51
34	Practical thermoreflectance design for optical characterization of layer semiconductors. <i>Review of Scientific Instruments</i> , 2004, 75, 1098-1102.	1.3	50
35	Optical property of the near band-edge transitions in rhenium disulfide and diselenide. <i>Journal of Alloys and Compounds</i> , 2004, 383, 74-79.	5.5	49
36	Synthesis of In ₂ S ₃ and Ga ₂ S ₃ crystals for oxygen sensing and UV photodetection. <i>Sensors and Actuators A: Physical</i> , 2016, 245, 119-126.	4.1	49

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37	Complete-series excitonic dipole emissions in few layer ReS ₂ and ReSe ₂ observed by polarized photoluminescence spectroscopy. Nano Energy, 2019, 56, 641-650.	16.0	49
38	Photoreflectance study of the excitonic transitions of rhenium disulphide layer compounds. Physical Review B, 2002, 66, .	3.2	48
39	Crystal structure and electronic structure of GaSe _{1-x} S _x series layered solids. Journal of Crystal Growth, 2005, 279, 321-328.	1.5	46
40	Polarized Band-Edge Emission and Dichroic Optical Behavior in Thin Multilayer GeS. Advanced Optical Materials, 2017, 5, 1600814.	7.3	45
41	Ultraefficient Ultraviolet and Visible Light Sensing and Ohmic Contacts in High-Mobility InSe Nanoflake Photodetectors Fabricated by the Focused Ion Beam Technique. ACS Applied Materials & Interfaces, 2018, 10, 5740-5749.	8.0	45
42	The electrical transport properties of ReS ₂ and ReSe ₂ layered crystals. Solid State Communications, 1999, 111, 635-640.	1.9	44
43	Optical properties of GaSe _{1-x} S _x series layered semiconductors grown by vertical Bridgman method. Materials Chemistry and Physics, 2004, 88, 313-317.	4.0	44
44	Characterization of indirect and direct interband transitions of anatase TiO ₂ by thermoreflectance spectroscopy. Applied Physics Letters, 2008, 93, .	3.3	40
45	Transport properties in semiconducting NbS ₂ nanoflakes. Applied Physics Letters, 2014, 105, .	3.3	39
46	Effect of temperature on lateral growth of ZnO grains grown by MOCVD. Ceramics International, 2010, 36, 69-73.	4.8	38
47	Amorphous effect on the advancing of wide-range absorption and structural-phase transition in β -In ₂ Se ₃ polycrystalline layers. Scientific Reports, 2014, 4, 4764.	3.3	38
48	Optical study of the structural change in ReS ₂ single crystals using polarized thermoreflectance spectroscopy. Optics Express, 2005, 13, 8.	3.4	37
49	Cleavage tendency of anisotropic two-dimensional materials: $\langle \text{Re} \rangle \times \langle X \rangle$. Physical Review B, 2017, 96, .	3.2	36
50	Polarization Photoelectric Conversion in Layered GeS. Advanced Optical Materials, 2018, 6, 1701194.	7.3	36
51	Analog Circuit Applications Based on All-2D Ambipolar ReSe ₂ Field-Effect Transistors. Advanced Functional Materials, 2019, 29, 1809011.	14.9	36
52	Polarization sensitive behaviour of the band-edge transitions in ReS ₂ and ReSe ₂ layered semiconductors. Journal of Physics Condensed Matter, 2004, 16, 5937-5944.	1.8	33
53	Interplay Between Cr Dopants and Vacancy Clustering in the Structural and Optical Properties of WSe ₂ . ACS Nano, 2017, 11, 11162-11168.	14.6	33
54	Temperature-dependent ultraviolet photoluminescence in hierarchical Zn, ZnO and ZnO/Zn nanostructures. Nanoscale, 2019, 11, 13385-13396.	5.6	32

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55	Photoconductance and photoresponse of layer compound photodetectors in the UV-visible region. Review of Scientific Instruments, 2006, 77, 113102.	1.3	30
56	Temperature-dependent photoconductivity in In_2S_3 single crystals. Journal of Applied Physics, 2010, 108, .	2.5	29
57	Multifunctional full-visible-spectrum optoelectronics based on a van der Waals heterostructure. Nano Energy, 2019, 66, 104107.	16.0	28
58	Low-Voltage Operational, Low-Power Consuming, and High Sensitive Tactile Switch Based on 2D Layered InSe Tribotronics. Advanced Functional Materials, 2019, 29, 1809119.	14.9	28
59	Room-temperature wide-range photoluminescence and semiconducting characteristics of two-dimensional pure metallic Zn nanoplates. RSC Advances, 2012, 2, 2123.	3.6	26
60	Thickness-tunable band gap modulation in In_2Se_3 . RSC Advances, 2013, 3, 24896.	3.6	26
61	Ternary $\text{ReS}_2(1-x)\text{Se}_{2x}$ alloy saturable absorber for passively Q-switched and mode-locked erbium-doped all-fiber lasers. Photonics Research, 2019, 7, 283.	7.0	26
62	Preparation and characterization of Ni-incorporated FeS_2 single crystals. Journal of Crystal Growth, 2004, 270, 535-541.	1.5	25
63	Visible luminescence and structural property of $\text{GaSe}_{1-x}\text{S}_x$ ($0 \leq x \leq 1$) series layered crystals. Solid State Communications, 2005, 136, 591-594.	1.9	25
64	Electrical and optical anisotropic properties of rhenium-doped molybdenum disulphide. Journal of Alloys and Compounds, 2001, 317-318, 208-212.	5.5	24
65	Thermoreflectance characterization of band-edge excitonic transitions in CuAlS_2 ultraviolet solar-cell material. Applied Physics Letters, 2010, 96, .	3.3	23
66	Large-area nanoscale farmland-like surfaces of one-dimensional NbO_2 nanorods with multi-growth directions: studies on the purple-blue photoluminescence and low-field electron emissions. Journal of Materials Chemistry C, 2014, 2, 8667-8672.	5.5	23
67	High-Mobility InSe Transistors: The Nature of Charge Transport. ACS Applied Materials & Interfaces, 2019, 11, 35969-35976.	8.0	23
68	High-responsivity broad-band sensing and photoconduction mechanism in direct-Gap In_2Se_3 nanosheet photodetectors. Nanotechnology, 2020, 31, 465201.	2.6	23
69	Direct vapor transport synthesis of ZnGa_2O_4 nanowires with superior photocatalytic activity. Journal of Alloys and Compounds, 2013, 555, 325-329.	5.5	22
70	Dynamic tungsten diselenide nanomaterials: supramolecular assembly-induced structural transition over exfoliated two-dimensional nanosheets. Chemical Science, 2018, 9, 5452-5460.	7.4	22
71	Inverse paired-pulse facilitation in neuroplasticity based on interface-boosted charge trapping layered electronics. Nano Energy, 2020, 77, 105258.	16.0	22
72	Study of Structural, Thermoelectric, and Photoelectric Properties of Layered Tin Monochalcogenides SnX ($X = \text{S}, \text{Se}$) for Energy Application. ACS Applied Energy Materials, 2020, 3, 4896-4905.	5.1	22

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73	Thermoelectric properties of Zn _{1-x} Sb alloys doped with In. Journal of Alloys and Compounds, 2009, 480, 73-75.	5.5	21
74	Influence of rhenium on the structural and optical properties of molybdenum disulfide. Japanese Journal of Applied Physics, 2015, 54, 04DH05.	1.5	21
75	Curvature-dependent flexible light emission from layered gallium selenide crystals. RSC Advances, 2018, 8, 2733-2739.	3.6	21
76	The band-edge excitons observed in few-layer NiPS ₃ . Npj 2D Materials and Applications, 2021, 5, .	7.9	21
77	Optical characterization of band-edge property of In ₆ S ₇ compound. Applied Physics Letters, 2012, 100, .	3.3	20
78	Piezoreflectance study of near band edge excitonic-transitions of mixed-layered crystal Mo(S _x Se _{1-x}) ₂ solid solutions. Journal of Applied Physics, 2014, 115, .	2.5	20
79	Structural phase transition and erasable optically memorized effect in layered In ₂ Se ₃ crystals. Journal of Applied Physics, 2014, 115, .	2.5	20
80	Optical Characterization of Strong UV Luminescence Emitted from the Excitonic Edge of Nickel Oxide Nanotowers. Scientific Reports, 2015, 5, 15856.	3.3	20
81	Nanowire Grid Polarization and Polarized Excitonic Emission Observed in Multilayer GaTe. Journal of Physical Chemistry Letters, 2020, 11, 608-617.	4.6	20
82	Tuning Interface Barrier in 2D BP/ReSe ₂ Heterojunctions in Control of Optoelectronic Performances and Energy Conversion Efficiencies. ACS Photonics, 2020, 7, 2886-2895.	6.6	20
83	Direct and indirect light emissions from layered ReS ₂ Se _x (0 < x < 1) crystals. Optics Letters, 2019, 44, 1913-1916.	2.6	19
84	Few-layer ReS ₂ Se _x nanoflakes for noise-like pulse generation in a mode-locked ytterbium-doped fiber laser. Journal of Materials Chemistry C, 2019, 7, 6900-6904.	5.5	19
85	Piezoreflectance study of band-edge excitons of ReS ₂ Se _x single crystals. Physical Review B, 1998, 58, 12575-12578.	3.2	18
86	Temperature dependence piezoreflectance study of the effect of doping MoS ₂ with rhenium. Journal of Physics Condensed Matter, 2000, 12, 3441-3449.	1.8	18
87	Multilayer GaSe/InSe Heterointerface-Based Devices for Charge Transport and Optoelectronics. ACS Applied Nano Materials, 2020, 3, 11769-11776.	5.0	18
88	Optical and Thermoelectric Properties of Surface-Oxidation Sensitive Layered Zirconium Dichalcogenides ZrS ₂ Se _x (x = 0, 1, 2) Crystals Grown by Chemical Vapor Transport. Crystals, 2020, 10, 327.	2.2	18
89	Photoactive Electro-Optically Controlled Visual Perception Memory for Emulating Synaptic Metaplasticity and Hebbian Learning. Advanced Functional Materials, 2021, 31, 2105345.	14.9	18
90	Upconversion of Light into Bright Intravalley Excitons via Dark Intervalley Excitons in hBN-Encapsulated WSe ₂ Monolayers. ACS Nano, 2021, 15, 19165-19174.	14.6	18

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91	Van der Waals Heterostructure Photodetectors with Bias-Selectable Infrared Photoresponses. ACS Applied Materials & Interfaces, 2022, 14, 32665-32674.	8.0	18
92	The study of surface photoconductive response in indium sulfide crystals. Journal Physics D: Applied Physics, 2010, 43, 415301.	2.8	17
93	Probing negatively charged and neutral excitons in MoS ₂ /hBN and hBN/MoS ₂ /hBN van der Waals heterostructures. Nanotechnology, 2021, 32, 145717.	2.6	17
94	Optical anisotropy of Au-doped ReS ₂ crystals. Journal of Alloys and Compounds, 2009, 480, 94-96.	5.5	16
95	Optical Characterization of Structural Quality in the Formation of In ₂ O ₃ Thin-Film Nanostructures. Journal of Physical Chemistry C, 2016, 120, 21983-21989.	3.1	16
96	NIR and UV enhanced photon detector made by diindium trichalcogenides. Optical Materials Express, 2013, 3, 1420.	3.0	15
97	Optical-memory switching and oxygen detection based on the CVT grown $\hat{\Gamma}^3$ - and $\hat{\Gamma}^\pm$ -phase In ₂ Se ₃ . Sensors and Actuators B: Chemical, 2015, 209, 811-819.	7.8	15
98	Synthesis and Optical Characterization of Oxygen-Incorporated ZnS(1 <i>x</i>)O(<i>x</i>) for UV-Visible Color Palette Light-Emission Matter. ACS Omega, 2017, 2, 4514-4523.	3.5	15
99	Temperature Dependence of the Band-Edge Transitions of ZnCdBeSe. Japanese Journal of Applied Physics, 2004, 43, 459-466.	1.5	14
100	Growth and characterization of tungsten and molybdenum-doped ReSe ₂ single crystals. Journal of Alloys and Compounds, 2004, 383, 63-68.	5.5	14
101	Characterization of nitrogen doped p-type ZnO thin films prepared by reactive ion beam sputter deposition. Surface and Coatings Technology, 2013, 231, 492-495.	4.8	14
102	The structure and opto-thermo electronic properties of a new (Bi(Bi ₂ S ₃) ₉ l ₃) _{2/3} hexagonal nano-/micro-rod. Chemical Communications, 2017, 53, 3741-3744.	4.1	14
103	In-Plane Axially Enhanced Photocatalysis by Re ₄ Diamond Chains in Layered ReS ₂ . Journal of Physical Chemistry C, 2018, 122, 18776-18784.	3.1	14
104	Ga ₂ Se ₃ Defect Semiconductors: The Study of Direct Band Edge and Optical Properties. ACS Omega, 2020, 5, 18527-18534.	3.5	14
105	Dual phase two-color emission observed in van der Waals GaTe planes. Applied Surface Science, 2021, 542, 148593.	6.1	14
106	Temperature dependent study of the band edge excitons of ReS ₂ and ReSe ₂ . Journal of Alloys and Compounds, 1997, 262-263, 92-96.	5.5	13
107	Polarized electrolyte-electroreflectance study of ReS ₂ and ReSe ₂ layered semiconductors. Journal of Physics Condensed Matter, 2001, 13, 8145-8152.	1.8	13
108	Characterization of near band-edge properties of synthetic p-FeS ₂ iron pyrite from electrical and photoconductivity measurements. Journal of Alloys and Compounds, 2006, 422, 321-327.	5.5	13

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109	Comprehensive Characterization of AlGaAs ^x InGaAs ^{1-x} GaAs Composite-Channel High-Electron Mobility Transistor. <i>Journal of the Electrochemical Society</i> , 2007, 154, H951.	2.9	13
110	Surface sensing behavior and band edge properties of AgAlS ₂ : Experimental observations in optical, chemical, and thermoreflectance spectroscopy. <i>AIP Advances</i> , 2012, 2, .	1.3	13
111	Preparation and characterization of molybdenum-doped ReS ₂ single crystals. <i>Journal of Physics Condensed Matter</i> , 2002, 14, 4737-4746.	1.8	12
112	Optical anisotropy of ZnO nanocrystals on sapphire by thermoreflectance spectroscopy. <i>Optics Letters</i> , 2007, 32, 2765.	3.3	12
113	Effect of Cr on the Structure and Property of Mo _{1-x} Cr _x Se ₂ (0 ≤ x ≤ 0.2) and Cr ₂ Se ₃ . <i>ACS Applied Electronic Materials</i> , 2019, 1, 370-378.	4.3	12
114	Thermoreflectance study of the electronic structure of Ge(Se _{1-x} S _x) ₂ . <i>Physical Review B</i> , 2005, 72, .	3.2	11
115	Practical photoluminescence and photoreflectance spectroscopic system for optical characterization of semiconductor devices. <i>Optics Express</i> , 2005, 13, 3951.	3.4	11
116	Electronic Structure and E ₁ Excitons of CuInS ₂ Energy-Related Crystals Studied by Temperature-Dependent Thermoreflectance Spectroscopy. <i>Journal of the Electrochemical Society</i> , 2010, 157, H219.	2.9	11
117	Synthesis of ¹²⁵ I-Ga ₂ O ₃ nanowires as a broadband emitter. <i>Applied Physics A: Materials Science and Processing</i> , 2011, 102, 105-108.	2.3	11
118	The study of below and above band-edge imperfection states in In ₂ S ₃ solar energy materials. <i>Physica B: Condensed Matter</i> , 2012, 407, 3052-3055.	2.7	11
119	An all two-dimensional vertical heterostructure graphene/CuInP ₂ S ₆ /MoS ₂ for negative capacitance field effect transistor. <i>Nanotechnology</i> , 2022, 33, 125703.	2.6	11
120	Piezoreflectance study of the band-edge excitons of ReS ₂ . <i>Solid State Communications</i> , 1997, 103, 19-23.	1.9	10
121	Dichroic optical and electrical properties of rhenium dichalcogenides layer compounds. <i>Journal of Alloys and Compounds</i> , 2007, 442, 245-248.	5.5	10
122	Single crystal growth and characterization of copper aluminum indium disulfide chalcopyrites. <i>Journal of Crystal Growth</i> , 2011, 317, 52-59.	1.5	10
123	The study of rapid thermal annealing on arsenic-doped ZnO for the p-type ZnO formation. <i>Journal of Crystal Growth</i> , 2013, 362, 193-196.	1.5	10
124	Optical behavior and structural property of CuAlS ₂ and AgAlS ₂ wide-bandgap chalcopyrites. <i>Applied Optics</i> , 2014, 53, E7.	1.8	10
125	Dichroic Electro-Optical Behavior of Rhenium Sulfide Layered Crystal. <i>Crystal Structure Theory and Applications</i> , 2013, 02, 65-69.	0.1	10
126	Structural and luminescent property of gallium chalcogenides GaSe _{1-x} S _x layer compounds. <i>Journal of Materials Science: Materials in Electronics</i> , 2009, 20, 207-210.	2.2	9

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127	Optical and electrical characteristics of GaAs/InGaAs quantum-well device. Journal of Alloys and Compounds, 2009, 471, 567-569.	5.5	9
128	Optical investigation of band-edge structure and built-in electric field of AlGaIn/GaN heterostructures by means of thermoreflectance, photoluminescence, and contactless electroreflectance spectroscopy. Optics Letters, 2009, 34, 3604.	3.3	9
129	Polarized-thermoreflectance study of the band-edge transitions in Cu _{0.5} Al _{0.5} In _{0.5} S ₂ solar-energy related crystal. Optics Express, 2010, 18, 3820.	3.4	9
130	The study of flexible emission and photoconductivity in 2D layered InSe toward an applicable 1000-nm light emitter and absorber. Applied Physics A: Materials Science and Processing, 2017, 123, 1.	2.3	9
131	Piezoreflectance and Raman Characterization of Mo _{1-x} W _x S ₂ Layered Mixed Crystals. Solid State Phenomena, 2011, 170, 55-59.	0.3	8
132	Temperature Dependent Crystal-Field Splitting and Band-Edge Characteristic in Cu _{0.5} (Al _x In _{1-x})S ₂ (0 ≤ x ≤ 1) Series Solar Energy Materials. Journal of the Electrochemical Society, 2011, 158, H554.	2.9	8
133	Optical and photodetector properties of stripe-like InS crystal. RSC Advances, 2016, 6, 97445-97448.	3.6	8
134	Temperature dependence of direct and indirect band gaps of Bi ₁₃ Ir ₂ S ₁₈ hexagonal rod crystals. Materials Chemistry and Physics, 2018, 206, 71-75.	4.0	8
135	The Study of Near-Band-Edge Property in Oxygen-Incorporated ZnS for Acting as an Efficient Crystal Photocatalyst. ACS Omega, 2018, 3, 6351-6359.	3.5	8
136	Synthesis, optical characterization, and environmental applications of In ₂ -Ga ₂ O ₃ nanowires. , 2019, , 67-90.		8
137	The Study of Optical Properties of III ₂ VI ₃ Defect Semiconductor Group Compounds Ga ₂ S ₃ , Ga ₂ Se ₃ , In ₂ S ₃ , and In ₂ Se ₃ . Advanced Photonics Research, 2021, 2, 2000110.	3.6	8
138	Investigations of Electron-Electron and Interlayer Electron-Phonon Coupling in van der Waals hBN/WSe ₂ /hBN Heterostructures by Photoluminescence Excitation Experiments. Materials, 2021, 14, 399.	2.9	8
139	Thermoreflectance characterization of the band-edge excitons observed in multilayered CuInP ₂ S ₆ . FlatChem, 2021, 29, 100290.	5.6	8
140	Formation of van der Waals Stacked p-n Homojunction Optoelectronic Device of Multilayered ReSe ₂ by Cr Doping. Advanced Optical Materials, 2022, 10, .	7.3	8
141	Inactivation of coupled respiration of mitochondria by inorganic arsenate and partial restoration by ATP. Biochemical and Biophysical Research Communications, 1972, 49, 690-697.	2.1	7
142	Characterization of Ge _{1-x} S _x series layered crystals grown by vertical Bridgman method. Journal of Crystal Growth, 2005, 281, 377-383.	1.5	7
143	Improved InAlGaP-based heterostructure field-effect transistors. Semiconductor Science and Technology, 2006, 21, 540-543.	2.0	7
144	In-plane anisotropic electrical and optical properties of gold-doped rhenium disulphide. Journal of Materials Science: Materials in Electronics, 2009, 20, 476-479.	2.2	7

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145	Carrier-capture-assisted optoelectronics based on van der Waals materials to imitate medicine-acting metaplasticity. <i>Npj 2D Materials and Applications</i> , 2021, 5, .	7.9	7
146	A practical and inexpensive design for measuring the radiation patterns and luminescent spectra of optoelectronic devices. <i>Review of Scientific Instruments</i> , 2001, 72, 3103-3107.	1.3	6
147	Electronic structure and optical property of $\text{As}_2(\text{Te}_{1-x}\text{S})_3$ and $\text{As}_2(\text{Te}_{1-x}\text{Se})_3$ crystals. <i>Journal of Alloys and Compounds</i> , 2011, 509, 7198-7204.	5.5	6
148	Composition Dependent Band Gaps of Single Crystal $\text{Cu}_{2-x}\text{ZnSn}(\text{S}_x\text{Se}_{1-x})_4$ Solid Solutions. <i>Solid State Phenomena</i> , 0, 194, 139-143.		6
149	Optical characterization of a $\text{GaAs}/\text{In}_{0.5}(\text{Al}_x\text{Ga}_{1-x})_{0.5}\text{P}/\text{GaAs}$ heterostructure cavity by piezoreflectance spectroscopy. <i>Optics Express</i> , 2007, 15, 13886.	3.4	5
150	Optical anisotropy of near band-edge transitions in zinc oxide nanostructures. <i>Journal of Alloys and Compounds</i> , 2009, 480, 50-53.	5.5	5
151	Nitrogen-doped ZnO prepared by capillaritron reactive ion beam sputtering deposition. <i>Applied Surface Science</i> , 2010, 256, 4153-4156.	6.1	5
152	Nitrogen Doping Effect on Optical Property of Gallium Oxide Nanowires. <i>ECS Journal of Solid State Science and Technology</i> , 2012, 1, P78-P81.	1.8	5
153	Cathodoluminescence and Field-Emission Properties of $\text{In}^{2+}\text{-Ga}_2\text{O}_3$ Nanobelts. <i>Journal of Electronic Materials</i> , 2012, 41, 3056-3061.	2.2	5
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